MUR2010CT THRU MUR2060CT

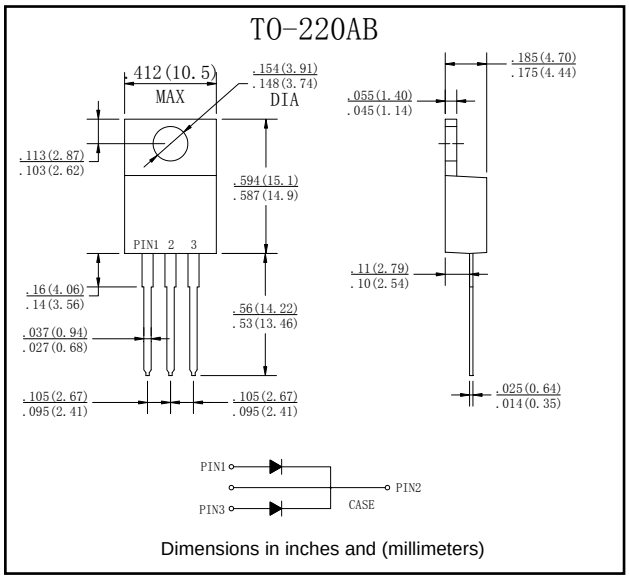
RoHS COMPLIANT

超快恢复整流二极管 Ultra-Fast Recovery Rectifier Diodes

■特征 Features

- I_o 20A
- V_{RRM} 100V~600V
- 玻璃钝化芯片 Glass passivated chip
- 耐正向浪涌电流能力高
  High surge forward current capability

■外形尺寸和印记 Outline Dimensions and Mark



Dimensions in inches and (millimeters)

■用途 Applications

- 快速整流用
  High speed switching

■极限值（绝对最大额定值）
Limiting Values（Absolute Maximum Rating）

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions		MUR-CT 2010	2015	2020	2040	2060
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V			100	150	200	400	600
平均整流输出电流 Average Rectified Output Current	I_o	A	60Hz正弦波，电阻负载 60Hz sine wave, R-load	用散热片 T_c =90℃ With heatsink T_c =90℃	20				
				无散热片 T_a =25℃ Without heatsink T_a =25℃	5				
正向（不重复）浪涌电流 Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz正弦波，一个周期，T_a=25℃ 60Hz sine wave, 1 cycle, T_a=25℃		125				
正向浪涌电流的平方对电流浪涌持续时间的积分值 Current Squared Time	I^2t	A^2s	1ms≤t＜8.3ms T_j=25℃,单个二极管 1ms≤t＜8.3ms T_j=25℃,Rating of per diode		65				
贮存温度 Storage Temperature	T_{stg}	℃			-55 ~ +150				
结温 Junction Temperature	T_j	℃			-55 ~ +150				

■电特性 （T_a=25℃ 除非另有规定）
Electrical Characteristics（T_a=25℃ Unless otherwise specified）

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition		MUR-CT 2010	2015	2020	2040	2060
正向峰值电压 Peak Forward Voltage	V_{FM}	V	I FM =10.0A		0.975			1.3	1.5
反向峰值电流 Peak Reverse Current	I_{RRM1}	μA	V_{RM} =V_{RRM}	T_a=25℃	10				
	I_{RRM2}			T_a=125℃	500				
反向恢复时间 Reverse Recovery Time	Trr	ns	I_F=0.5A I_{RM}=1A I_{RR}=0.25A		25			50	
热阻 Thermal Resistance	$R_{\theta J-C}$	℃/W	结和壳之间 Between junction and case		2.0				

■特性曲线（典型） Characteristics(Typical)

图1：正向电流降额曲线
FIG1: IF（AV）--Tc Derating

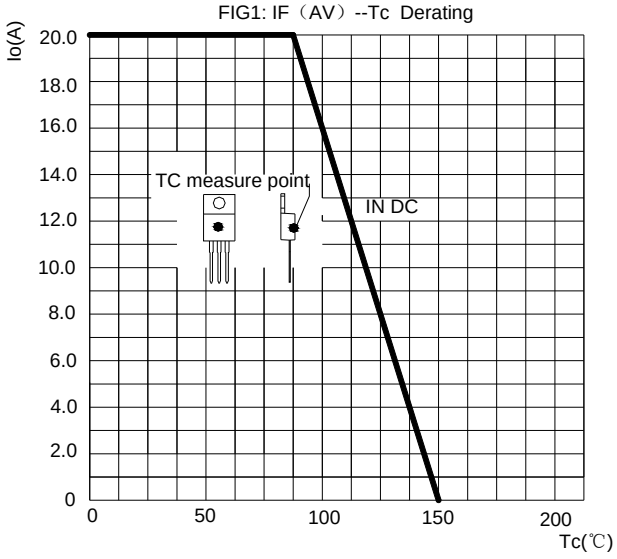


图2：耐正向浪涌电流曲线
FIG2:Surge Forward Current Capability

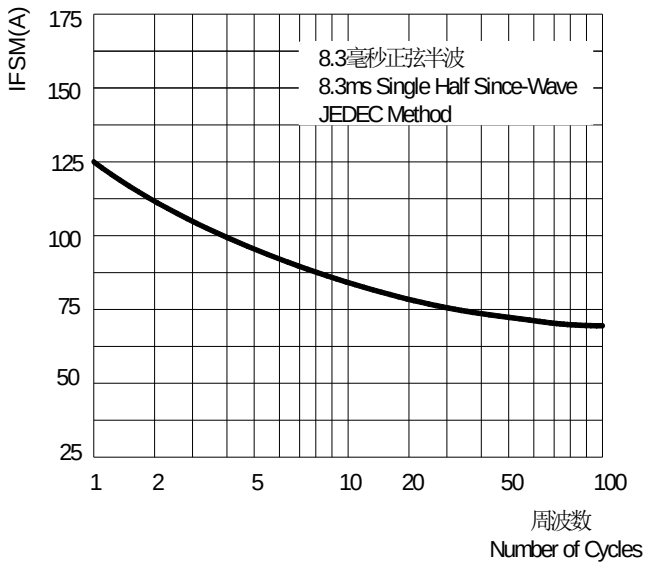


图3：正向电压曲线
FIG3:Instantaneous Forward Voltage

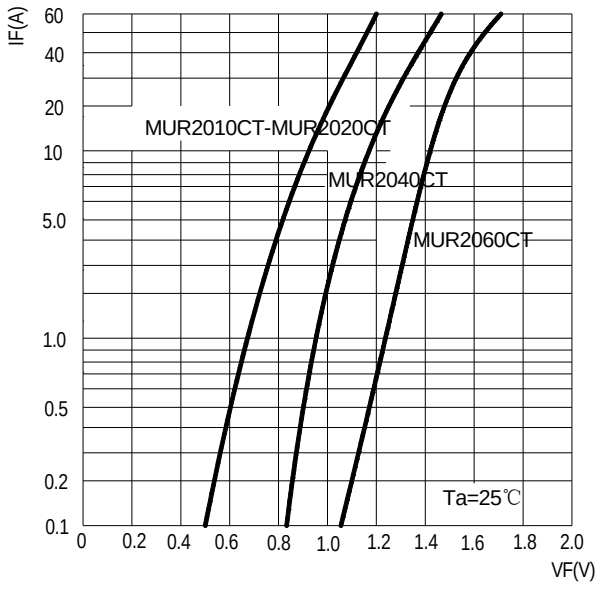


图4：反向电流曲线
FIG4:Typical Reverse Characteristics

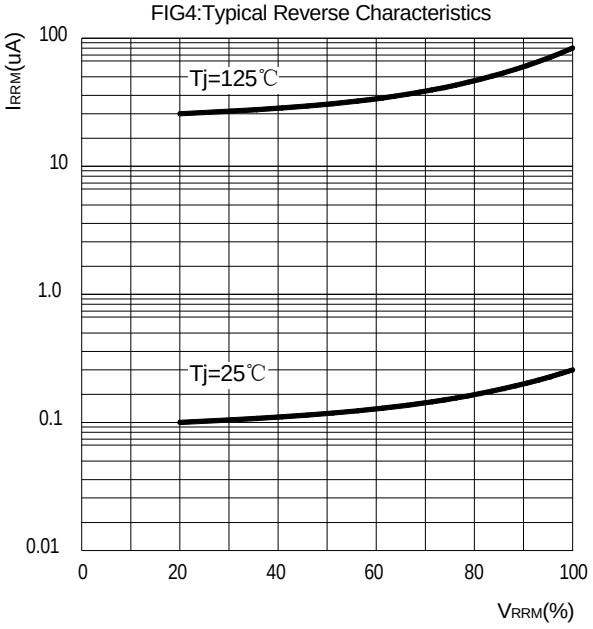


图5：反向恢复时间试验电路及测试波形示意图
FIG.5: Diagram of circuit and Testing wave form of reverse recovery time